Power MOSFET 20V, $38m\Omega$, 5.5A, Single N-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- High Speed Switching
- ESD Diode-Protected Gate
- Pb-Free and RoHS compliance
- Halogen Free compliance : MCH6421-TL-W

Typical Applications

- Load Switch
- Synchronous Boost Converter

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit		
Drain to Source Voltage	VDSS	20	V		
Gate to Source Voltage	VGSS	±12	V		
Drain Current (DC)	ID	5.5	Α		
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	22	Α		
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.5	W		
Junction Temperature	Tj	150	°C		
Storage Temperature	Tstg	-55 to +150	°C		

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

THERMAL REGISTANCE RATINGS					
Parameter	Symbol	Value	Unit		
Junction to Ambient When mounted on ceramic substrate (1200mm² × 0.8mm)	$R_{\theta JA}$	83.3	°C/W		

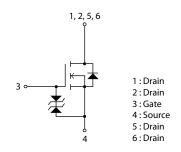


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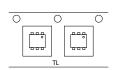
www.onsemi.com

VDSS	R _{DS} (on) Max	ID Max
	38mΩ@ 4.5V	
20V	61mΩ@ 2.5V	5.5A
	99mΩ@ 1.8V	

ELECTRICAL CONNECTION N-Channel



PACKING TYPE: TL





ORDERING INFORMATION

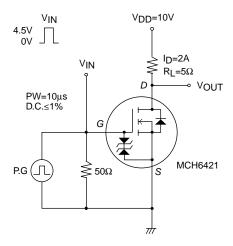
See detailed ordering and shipping information on page 5 of this data sheet.

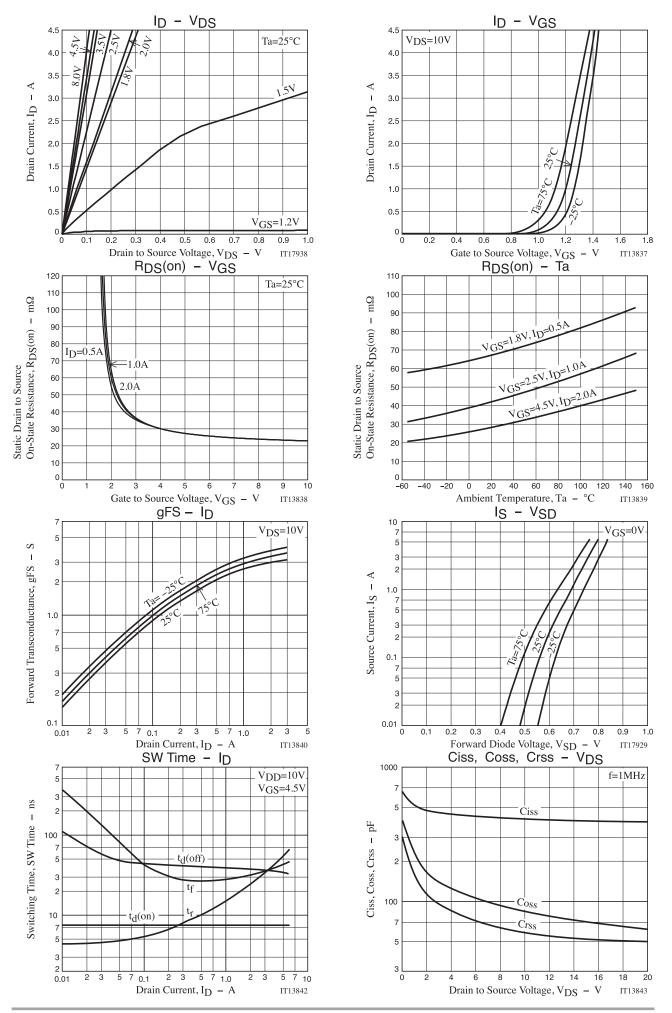
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

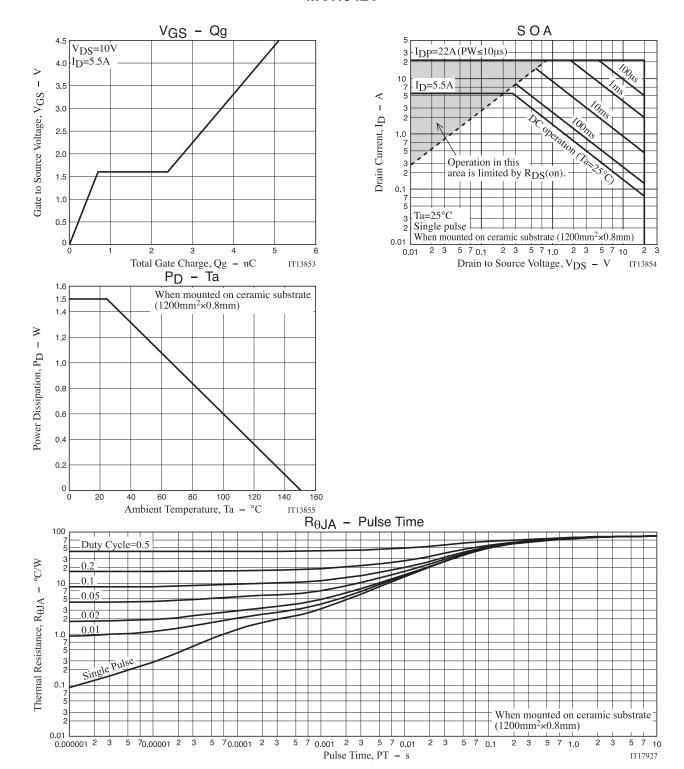
Parameter	Cumbal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Gate Threshold Voltage	V _G S(th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	gFS	V _{DS} =10V, I _D =2A 2.0		3.8		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	I _D =2A, V _G S=4.5V		29	38	mΩ
	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		43	61	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.8V		69	99	$m\Omega$
Input Capacitance	Ciss			410		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		84		pF
Reverse Transfer Capacitance	Crss			59		pF
Turn-ON Delay Time	t _d (on)			7.5		ns
Rise Time	tr	Con annuitied Took Circuit		26		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		38		ns
Fall Time	tf			32		ns
Total Gate Charge	Qg			5.1		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =5.5A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.7		nC
Forward Diode Voltage	V _{SD}	IS=5.5A, VGS=0V		0.8	1.2	V

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



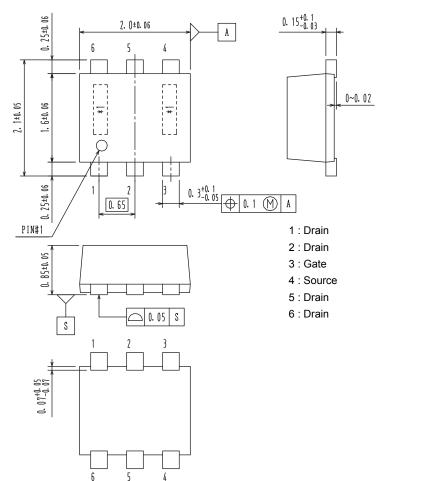




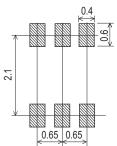
PACKAGE DIMENSIONS

unit : mm

SC-88FL / MCPH6 CASE 419AS ISSUE O



Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
MCH6421-TL-E	KV	SC-88FL / MCPH6 (Pb-Free)	3,000 / Tape & Reel
MCH6421-TL-W		SC-88FL / MCPH6 (Pb-Free / Halogen Free)	3,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the MCH6421 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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